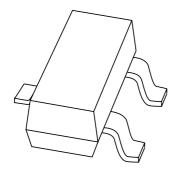
### **DISCRETE SEMICONDUCTORS**

# DATA SHEET



# BSR19; BSR19A NPN high voltage transistors

Product data sheet Supersedes data of 2004 Jan 13 2004 Mar 15



### NPN high voltage transistors

### BSR19; BSR19A

#### **FEATURES**

• Low current (max. 300 mA)

• High voltage (max. 160 V).

### **APPLICATIONS**

• General purpose switching and amplification

• Especially used for telephony applications.

### **DESCRIPTION**

NPN high-voltage transistor in a SOT23 plastic package. PNP complements: BSR20 and BSR20A.

### **MARKING**

TYPE NUMBER	MARKING CODE <sup>(1)</sup>
BSR19	56* or U35
BSR19A	57* or U36

#### Note

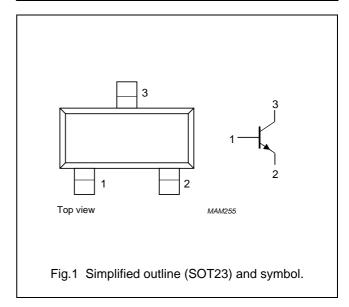
1. \* = p : Made in Hong Kong.

\* = t : Made in Malaysia.

\* = W : Made in China.

### **PINNING**

PIN	DESCRIPTION	
1	base	
2	emitter	
3	collector	



### **ORDERING INFORMATION**

TYPE	PACKAGE		
NUMBER	NAME	ME DESCRIPTION VERSION	
BSR19	_	plastic surface mounted package; 3 leads SOT2	
BSR19A	_	plastic surface mounted package; 3 leads SOT23	

## NPN high voltage transistors

BSR19; BSR19A

### **QUICK REFERENCE DATA**

SYMBOL	PARAMETER	CONDITIONS	MIN.	MAX.	UNIT
V <sub>CBO</sub>	collector-base voltage	open emitter			
	BSR19		_	160	V
	BSR19A		_	180	V
$V_{CEO}$	collector-emitter voltage	open base			
	BSR19		_	140	V
	BSR19A		_	160	V
I <sub>CM</sub>	peak collector current		_	600	mA
P <sub>tot</sub>	total power dissipation	$T_{amb} \le 25  ^{\circ}C$	_	250	mW
h <sub>FE</sub>	DC current gain	$I_C = 10 \text{ mA}; V_{CE} = 5 \text{ V}$			
	BSR19		60	_	
	BSR19A		80	_	
f <sub>T</sub>	transition frequency	I <sub>C</sub> = 10 mA; V <sub>CE</sub> = 10 V; f = 100 MHz	100	300	MHz

### **LIMITING VALUES**

In accordance with the Absolute Maximum Rating System (IEC 60134).

SYMBOL	PARAMETER	CONDITIONS	MIN.	MAX.	UNIT
V <sub>CBO</sub>	collector-base voltage	open emitter			
	BSR19		_	160	V
	BSR19A		_	180	V
V <sub>CEO</sub>	collector-emitter voltage	open base			
	BSR19		_	140	V
	BSR19A		_	160	V
V <sub>EBO</sub>	emitter-base voltage	open collector	_	6	V
I <sub>C</sub>	collector current (DC)		_	300	mA
I <sub>CM</sub>	peak collector current		_	600	mA
I <sub>B</sub>	base current (DC)		-	100	mA
P <sub>tot</sub>	total power dissipation	T <sub>amb</sub> ≤ 25 °C	_	250	mW
T <sub>stg</sub>	storage temperature		-65	+150	°C
Tj	junction temperature		_	150	°C
T <sub>amb</sub>	operating ambient temperature		-65	+150	°C

### THERMAL CHARACTERISTICS

SYMBOL	PARAMETER	CONDITIONS	VALUE	UNIT
R <sub>th(j-a)</sub>	thermal resistance from junction to ambient	note 1	500	K/W

### Note

1. Transistor mounted on an FR4 printed-circuit board.

# NPN high voltage transistors

BSR19; BSR19A

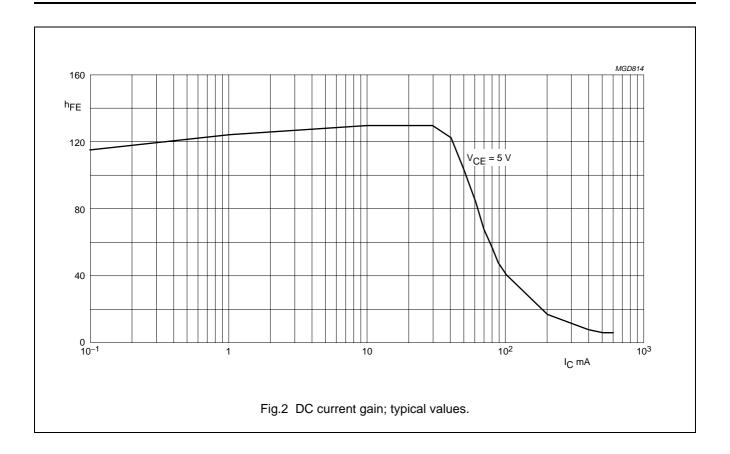
### **CHARACTERISTICS**

 $T_{amb}$  = 25 °C unless otherwise specified.

SYMBOL	PARAMETER	CONDITIONS	MIN.	MAX.	UNIT
I <sub>CBO</sub>	collector cut-off current				
	BSR19	I <sub>E</sub> = 0 A; V <sub>CB</sub> = 100 V	_	100	nA
		I <sub>E</sub> = 0 A; V <sub>CB</sub> = 100 V; T <sub>amb</sub> = 100 °C	_	100	μΑ
I <sub>CBO</sub>	collector cut-off current				
	BSR19A	I <sub>E</sub> = 0 A; V <sub>CB</sub> = 120 V	_	50	nA
		I <sub>E</sub> = 0 A; V <sub>CB</sub> = 120 V; T <sub>amb</sub> = 100 °C	_	50	μΑ
I <sub>EBO</sub>	emitter cut-off current	I <sub>C</sub> = 0 A; V <sub>EB</sub> = 4 V	_	50	nA
h <sub>FE</sub>	DC current gain	I <sub>C</sub> = 1 mA; V <sub>CE</sub> = 5 V			
	BSR19		60	_	
	BSR19A		80	_	
	DC current gain	I <sub>C</sub> = 10 mA; V <sub>CE</sub> = 5 V			
	BSR19		60	250	
	BSR19A		80	250	
	DC current gain	I <sub>C</sub> = 50 mA; V <sub>CE</sub> = 5 V			
	BSR19		20	_	
	BSR19A		30	_	
V <sub>CEsat</sub>	collector-emitter saturation voltage	I <sub>C</sub> = 10 mA; I <sub>B</sub> = 1 mA	_	150	mV
V <sub>CEsat</sub>	collector-emitter saturation voltage	$I_C = 50 \text{ mA}; I_B = 5 \text{ mA}$			
	BSR19		_	250	mV
	BSR19A		_	200	mV
C <sub>c</sub>	collector capacitance	I <sub>E</sub> = 0 A; V <sub>CB</sub> = 10 V; f = 1 MHz	_	6	pF
f <sub>T</sub>	transition frequency	I <sub>C</sub> = 10 mA; V <sub>CE</sub> = 10 V; f = 100 MHz	100	300	MHz

# NPN high voltage transistors

## BSR19; BSR19A



## NPN high voltage transistors

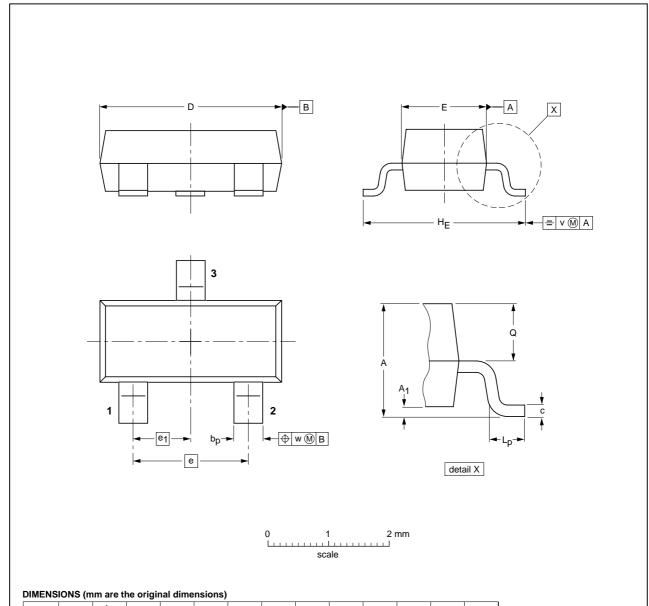
BSR19; BSR19A

### **PACKAGE OUTLINE**

UNIT

### Plastic surface-mounted package; 3 leads

SOT23



OUTLINE	REFERENCES		EUROPEAN	ICCUE DATE		
VERSION	IEC	JEDEC	JEITA		PROJECTION	ISSUE DATE
SOT23		TO-236AB				<del>-04-11-04</del> 06-03-16

 $\mathsf{L}_\mathsf{p}$ 

0.45

0.55

0.1

 $\mathbf{H}_{\mathbf{E}}$ 

2004 Mar 15 6

bp

0.38

max

0.9

### NPN high voltage transistors

BSR19; BSR19A

#### **DATA SHEET STATUS**

DOCUMENT STATUS <sup>(1)</sup>	PRODUCT STATUS <sup>(2)</sup>	DEFINITION
Objective data sheet	Development	This document contains data from the objective specification for product development.
Preliminary data sheet	Qualification	This document contains data from the preliminary specification.
Product data sheet	Production	This document contains the product specification.

#### **Notes**

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### **Contact information**

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